RENESAS BCR3PM-14LG

Triac Medium Power Use

REJ03G1557-0100					
Rev.1.00					
Jul 06, 2007					

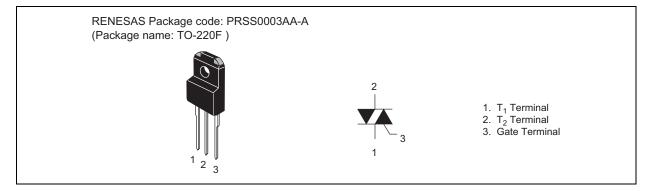
Features

- $I_{T(RMS)}: 3 A$
- V_{DRM} : 800 V (Tj = 125°C)
- I_{FGTI} , I_{RGTI} , I_{RGTII} : 30 mA
- Viso : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized: Yellow Card No. E223904

File No. E80271

Outline



Applications

Washing machine, inversion operation of capacitor motor, and other general controlling devices

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	Conditions
Falalletei	Symbol	14	Onic	
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	800	V	Tj = 125°C
		700	V	Tj = 150°C
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	840	V	

BCR3PM-14LG

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	3.0	A	Commercial frequency, sine full wave 360° conduction, Tc = 130°C
Surge on-state current	I _{TSM}	30	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	3.7	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	2	А	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, T ₁ • T ₂ • G terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	—	—	2.0	mA	Tj = 150°C, V _{DRM} applied
On-state voltage		V _{TM}	—	—	1.6	V	$Tc = 25^{\circ}C$, $I_{TM} = 4.5 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	$V_{\text{FGT}I}$	—	—	1.5	V	$Tj=25^{\circ}C,V_{D}=6~V,R_{L}=6~\Omega,$
	II	V _{RGTI}	—	—	1.5	V	R _G = 330 Ω
	III	V _{RGTIII}	_	—	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	—	—	30	mA	$Tj=25^{\circ}C,V_{D}=6~V,R_{L}=6~\Omega,$
	II	I _{RGTI}	_	—	30	mA	R _G = 330 Ω
	III	I _{RGTIII}	—	—	30	mA	
Gate non-trigger voltage		V _{GD}	0.2/0.1	—	—	V	$Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	—	—	5.2	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-stat commutating voltage ^{Note4}	e	(dv/dt)c	5/1		—	V/µs	Tj = 125°C/150°C

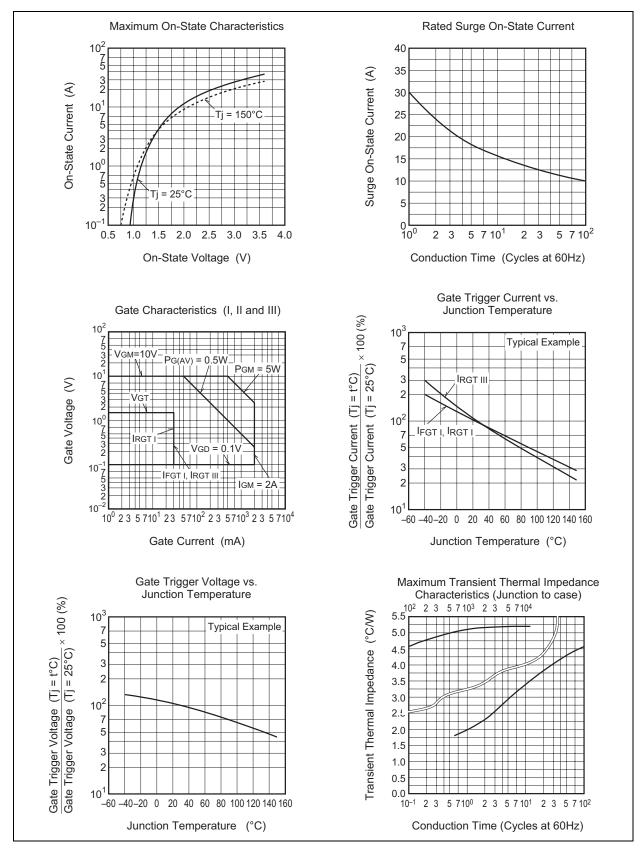
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th \ (c-f)}$ in case of greasing is 0.5°C/W.

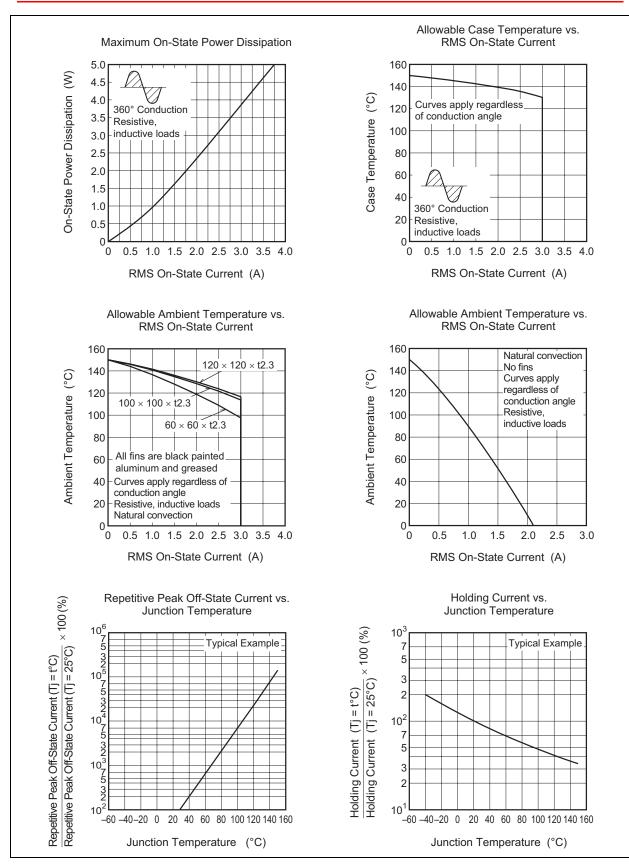
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = -1.5 A/ms	Main Current →Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage → Time (dv/dt)c V _D		

Performance Curves



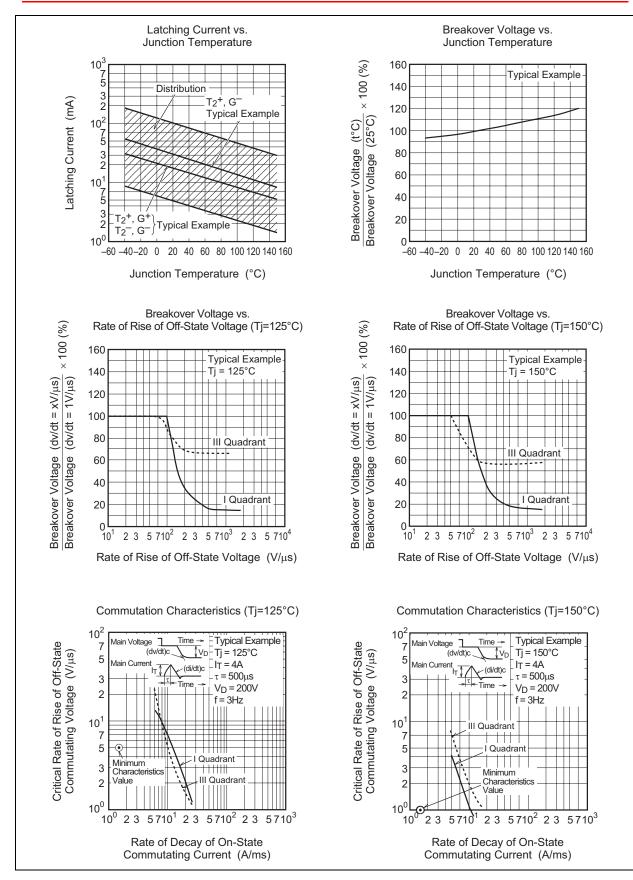
RENESAS



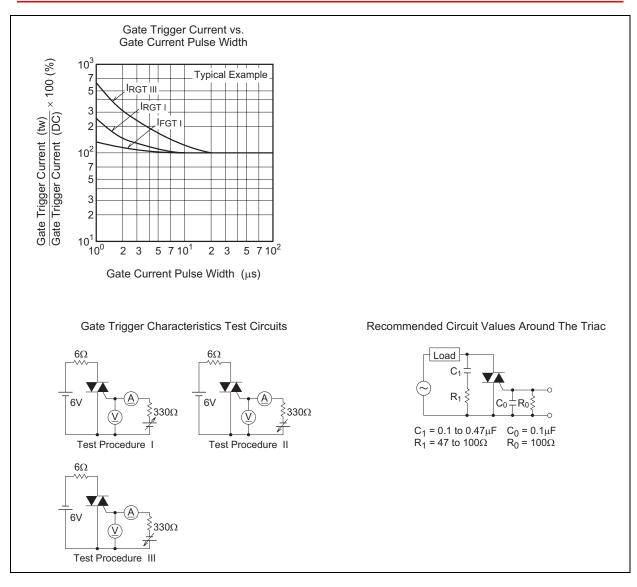
RENESAS

REJ03G1557-0100 Rev.1.00 Jul 06, 2007 Page 4 of 7

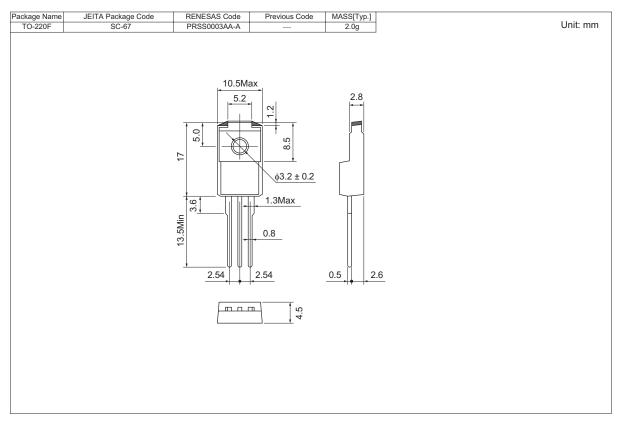
Downloaded from Elcodis.com electronic components distributor



RENESAS



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR3PM-14LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR3PM-14LG-A8

Note : Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- <section-header>

 Image: States

 Present States

 States

 Present State



http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510